TOSHIBA Field Effect Transistor with Built-in Schottky Barrier Diode

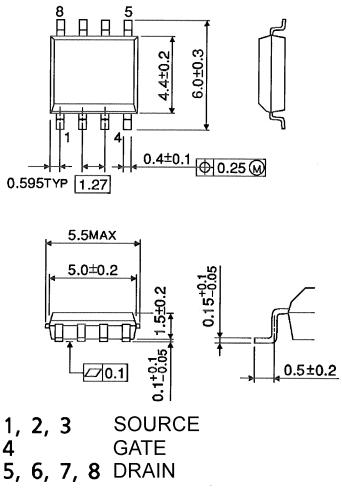
Silicon N-Channel MOS Type (U-MOS V-H)

TPC8A03-H

High Efficiency DC-DC Converter Applications
Notebook PC Applications
Portable Equipment Applications

- Built-in schottky barrier diode
  Low forward voltage: V_{DSF} = 0.6 V(max)
- High-speed switching
- Small gate charge: Q_{SW} = 8.4 nC (typ.)
- Low drain-source ON-resistance: $R_{DS\ (ON)}$ = 4.1 mΩ (typ.)
- High forward transfer admittance: $|Y_{fs}|$ = 54 S (typ.)
- Low leakage current: I_{DSS} = 100 μA (max) (V_{DS} = 30 V)
- Enhancement mode: V_{th} = 1.3 to 2.3 V (V_{DS} = 10 V, I_D = 1 mA)

Unit: mm



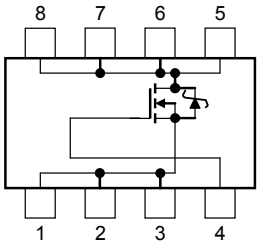
JEDEC	—
JEITA	—
TOSHIBA	2-6J1B

Weight: 0.085g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristic		Symbol	Rating	Unit
Drain-source voltage		V_{DSS}	30	V
Drain-gate voltage (R_{GS} = 20 kΩ)		V_{DGR}	30	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	DC (Note 1)	I_D	17	A
	Pulsed (Note 1)	I_{DP}	68	
Drain power dissipation (t = 10 s) (Note 2a)		P_D	1.9	W
Drain power dissipation (t = 10 s) (Note 2b)		P_D	1.0	W
Single-pulse avalanche energy (Note 3)		E_{AS}	188	mJ
Avalanche current		I_{AR}	17	A
Repetitive avalanche energy (Tc=25℃) (Note 4)		E_{AR}	0.108	mJ
Channel temperature		T_{ch}	150	°C
Storage temperature range		T_{stg}	−55 to 150	°C

Circuit Configuration



Note: For Notes 1 to 4, refer to the next page.

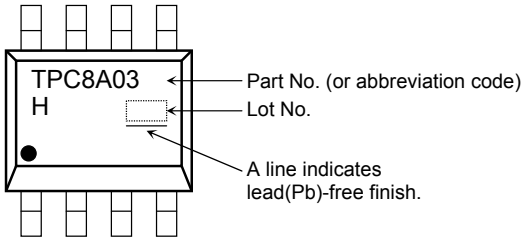
Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook (“Handling Precautions”/“Derating Concept and Methods”) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

This transistor is an electrostatic-sensitive device. Handle with care.

Thermal Characteristics

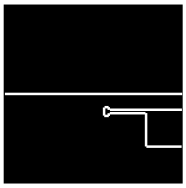
Characteristic	Symbol	Max	Unit
Thermal resistance, channel to ambient (t = 10 s) (Note 2a)	$R_{th\ (ch\text{-}a)}$	65.8	°C/W
Thermal resistance, channel to ambient (t = 10 s) (Note 2b)	$R_{th\ (ch\text{-}a)}$	125	°C/W

Marking (Note 5)



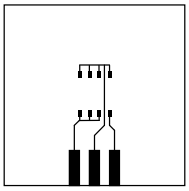
Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: (a) Device mounted on a glass-epoxy board (a) (b) Device mounted on a glass-epoxy board (b)



FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

(a)



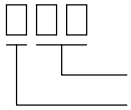
FR-4
25.4 × 25.4 × 0.8
(Unit: mm)

(b)

Note 3: V_{DD} = 24 V, T_{ch} = 25°C (initial), L = 0.5 mH, R_G = 25 Ω, I_{AR} = 17 A

Note 4: Repetitive rating: pulse width limited by maximum channel temperature

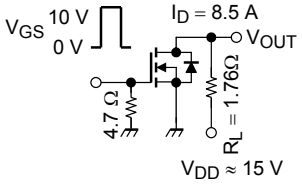
Note 5: * Weekly code: (Three digits)



Week of manufacture
(01 for first week of year, continuing up to 52 or 53)

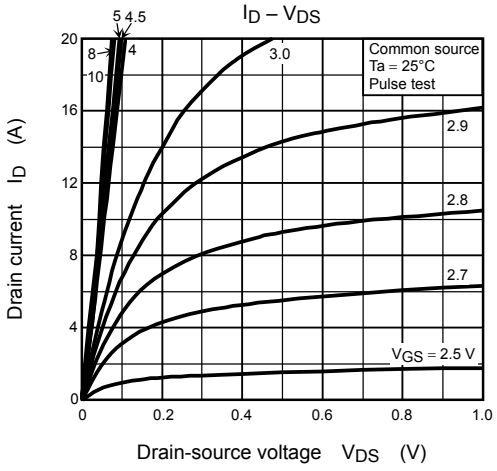
Year of manufacture
(The last digit of the calendar year)

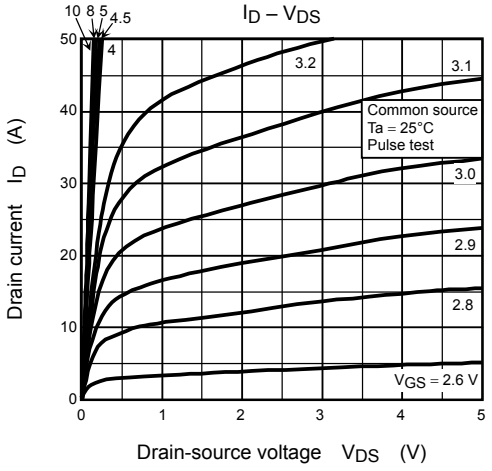
Electrical Characteristics (Ta = 25°C)

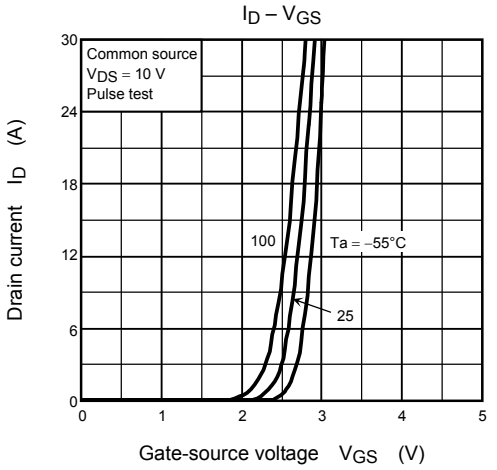
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Gate leakage current		I_{GSS}	V_{GS} = ±20 V, V_{DS} = 0 V	—	—	±100	nA
Drain cutoff current		I_{DSS}	V_{DS} = 30 V, V_{GS} = 0 V	—	—	100	μA
Drain-source breakdown voltage		$V_{(BR)\ DSS}$	I_D = 10 mA, V_{GS} = 0 V	30	—	—	V
		$V_{(BR)\ DSX}$	I_D = 10 mA, V_{GS} = −20 V	15	—	—	
Gate threshold voltage		V_{th}	V_{DS} = 10 V, I_D = 1 mA	1.3	—	2.3	V
Drain-source ON-resistance		$R_{DS\ (ON)}$	V_{GS} = 4.5 V, I_D = 8.5 A	—	5.1	7.0	mΩ
			V_{GS} = 10 V, I_D = 8.5 A	—	4.1	5.6	
Forward transfer admittance		$\|Y_{fs}\|$	V_{DS} = 10 V, I_D = 8.5 A	27	54	—	S
Input capacitance		C_{iss}	V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz	—	2640	3430	pF
Reverse transfer capacitance		C_{rss}		—	100	150	
Output capacitance		C_{oss}		—	610	—	
Gate resistance		rg	V_{DS} = 10 V, V_{GS} = 0 V, f = 5 MHz	—	1.0	1.5	Ω
Switching time	Rise time	t_r	 Duty ≤ 1%, t_w = 10 μs	—	3.6	—	ns
	Turn-on time	t_{on}		—	11.0	—	
	Fall time	t_f		—	7.2	—	
	Turn-off time	t_{off}		—	42	—	
Total gate charge (gate-source plus gate-drain)		Q_g	V_{DD} ≈ 24 V, V_{GS} = 10 V, I_D = 17 A	—	36	—	nC
			V_{DD} ≈ 24 V, V_{GS} = 5 V, I_D = 17 A	—	19	—	
Gate-source charge 1		Q_{gs1}	V_{DD} ≈ 24 V, V_{GS} = 10 V, I_D = 17 A	—	7.6	—	
Gate-drain (“Miller”) charge		Q_{gd}		—	5.0	—	
Gate switch charge		Q_{SW}		—	8.4	—	

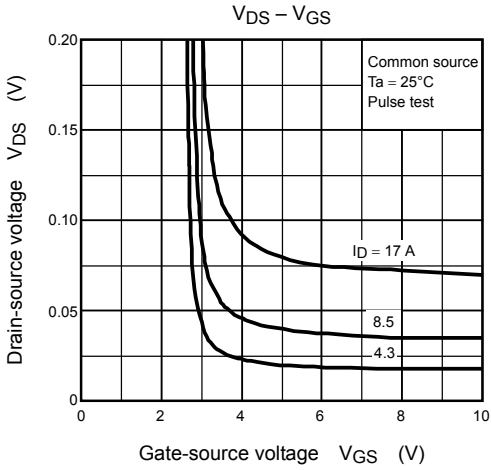
Source-Drain Ratings and Characteristics (Ta = 25°C)

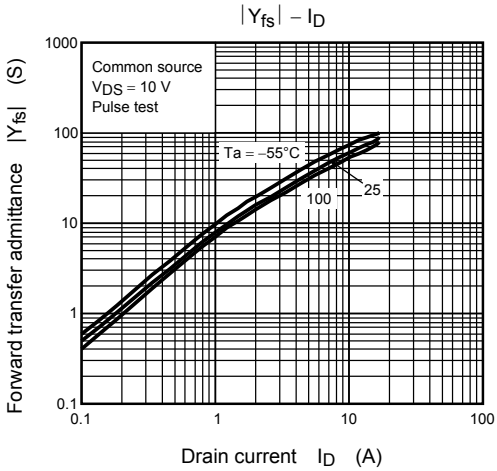
Characteristic		Symbol	Test Condition	Min	Typ.	Max	Unit
Peak forward current	Pulse (Note 1)	I_{FP}	—	—	—	68	A
Forward voltage (diode)		V_{DSF}	I_{DR} = 1 A, V_{GS} = 0 V	—	− 0.4	− 0.6	V
			I_{DR} = 17 A, V_{GS} = 0 V	—	—	− 1.2	V

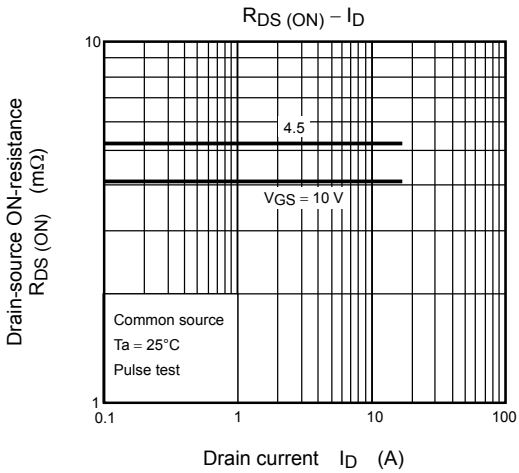




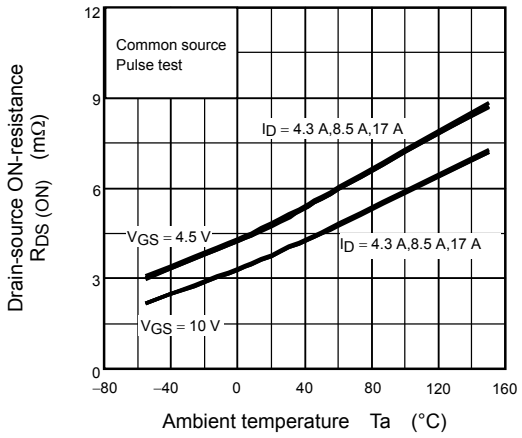




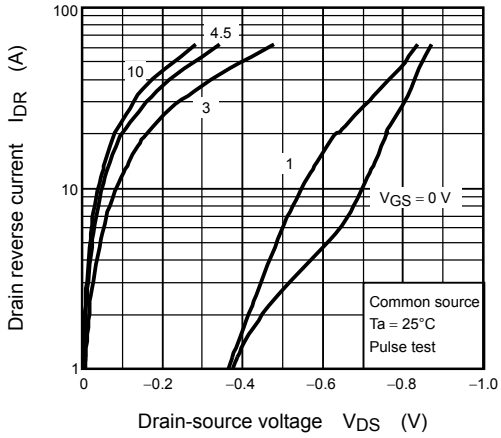




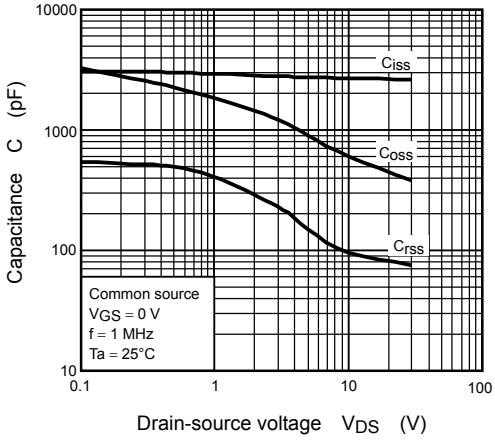
$R_{DS\ (ON)}$ – Ta



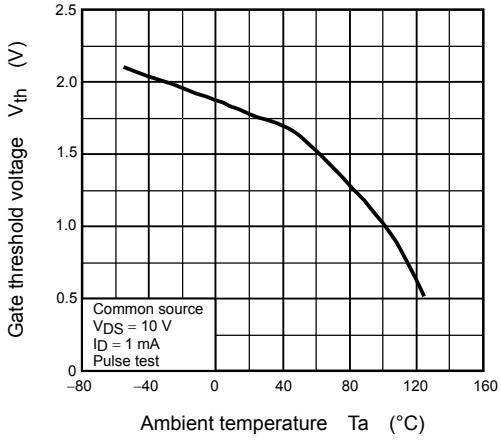
I_{DR} – V_{DS}



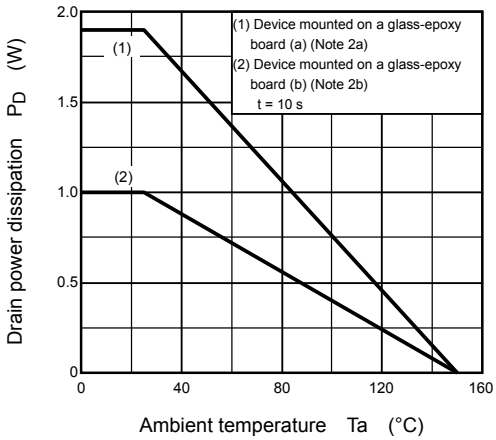
Capacitance – V_{DS}



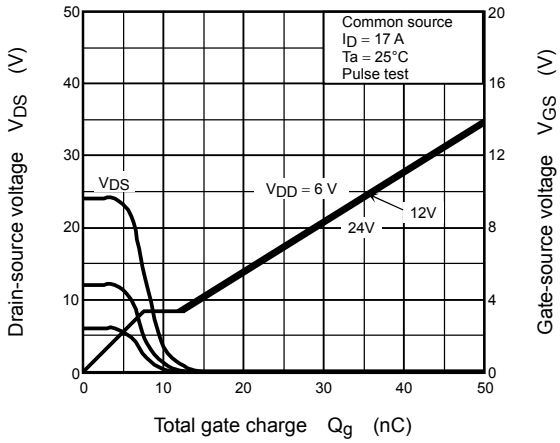
V_{th} – Ta

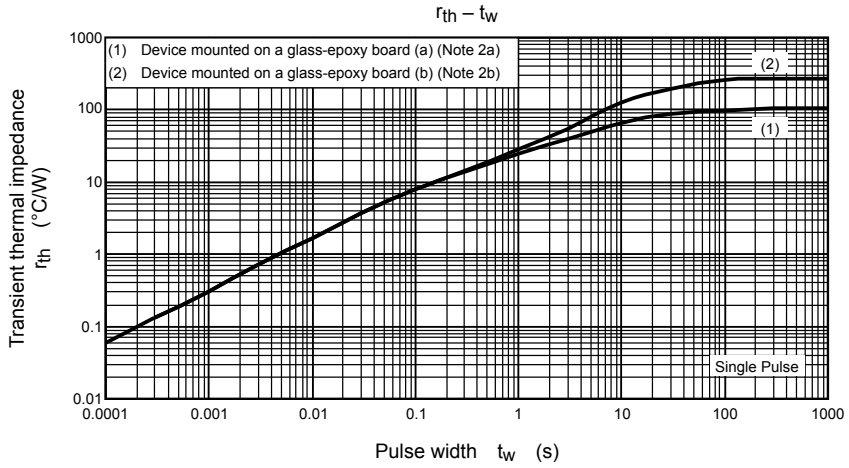


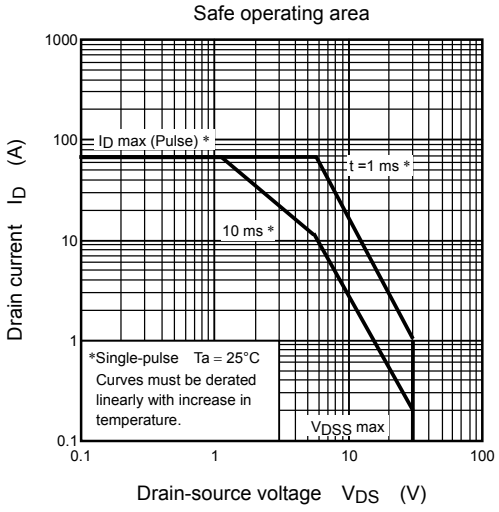
P_D – Ta



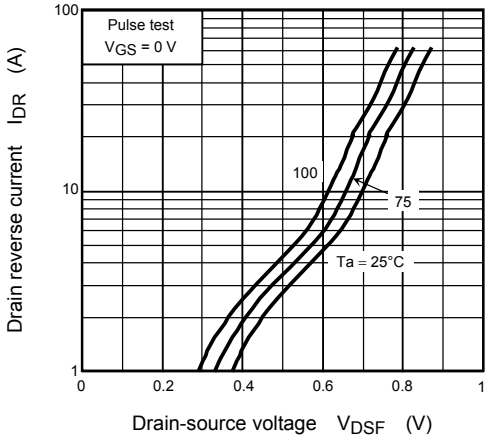
Dynamic input/output characteristics



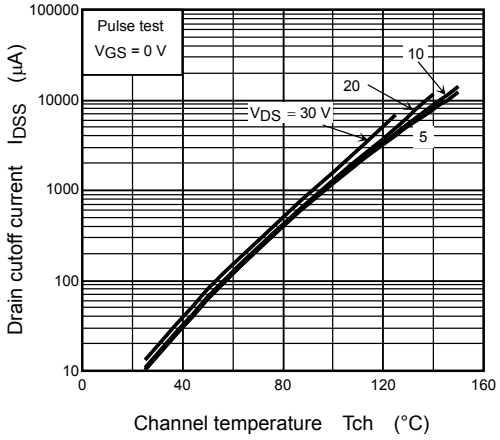




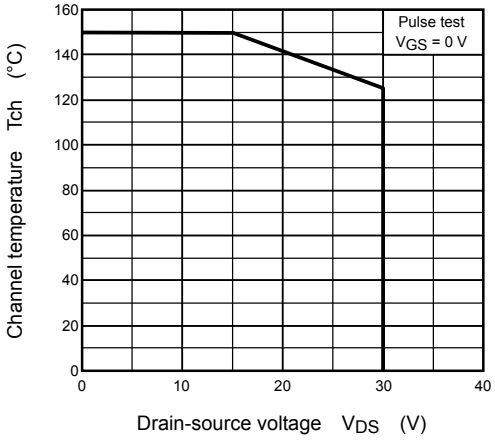
I_{DR} – V_{DSF}



I_{DSS} – Tch (typ.)



Tch – V_{DS}



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20070701-EN GENERAL

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